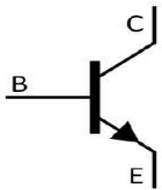


Rev.F Apr.-2017

SOT-23 NPN Silicon NPN transistor in a SOT-23 Plastic Package.

Low current, high voltage.

Telephony and professional communication equipment.

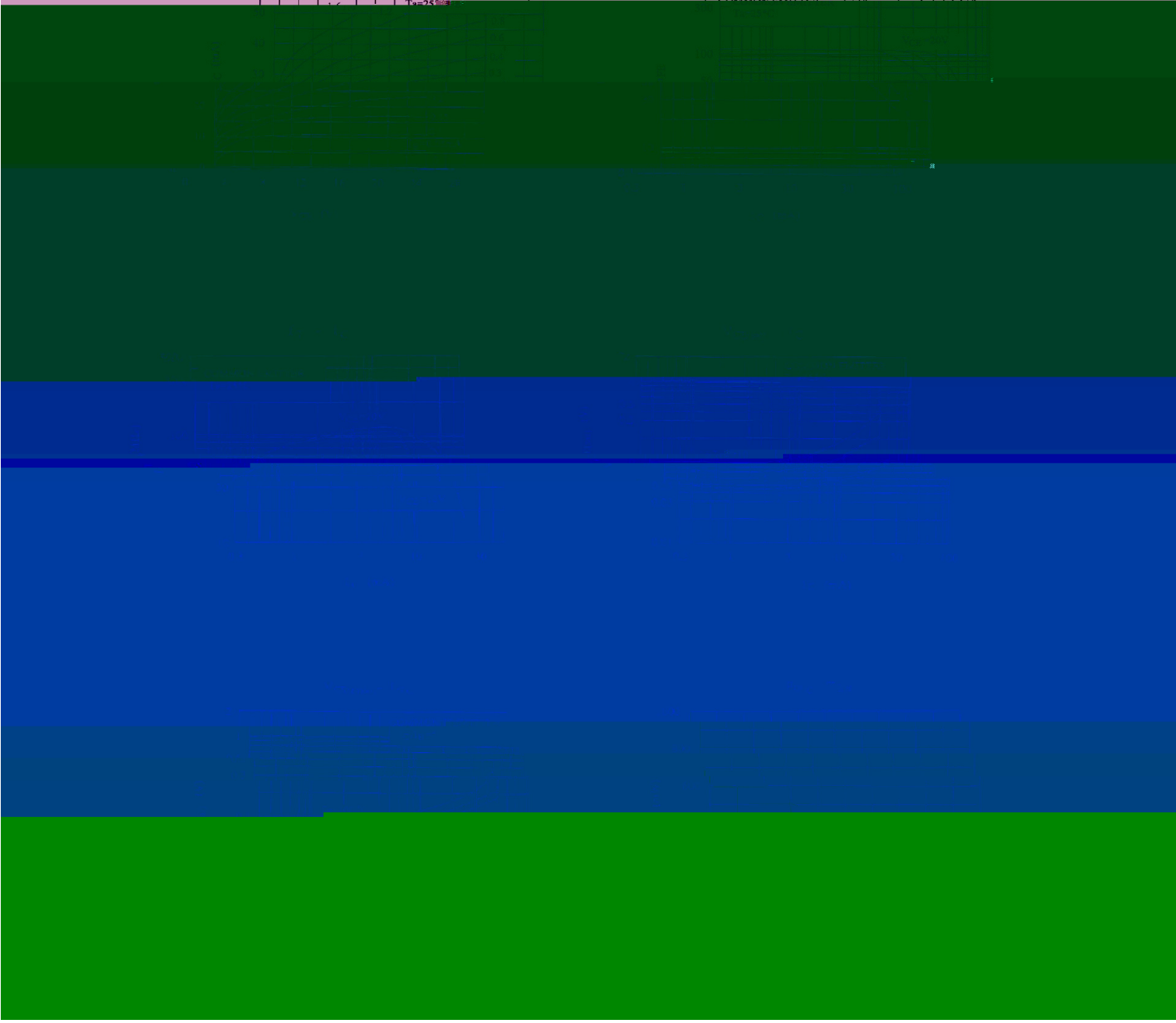


PIN1 Base PIN 2 Emitter PIN 3 Collector

h_{FE} Range	>50
Marking	H1XW

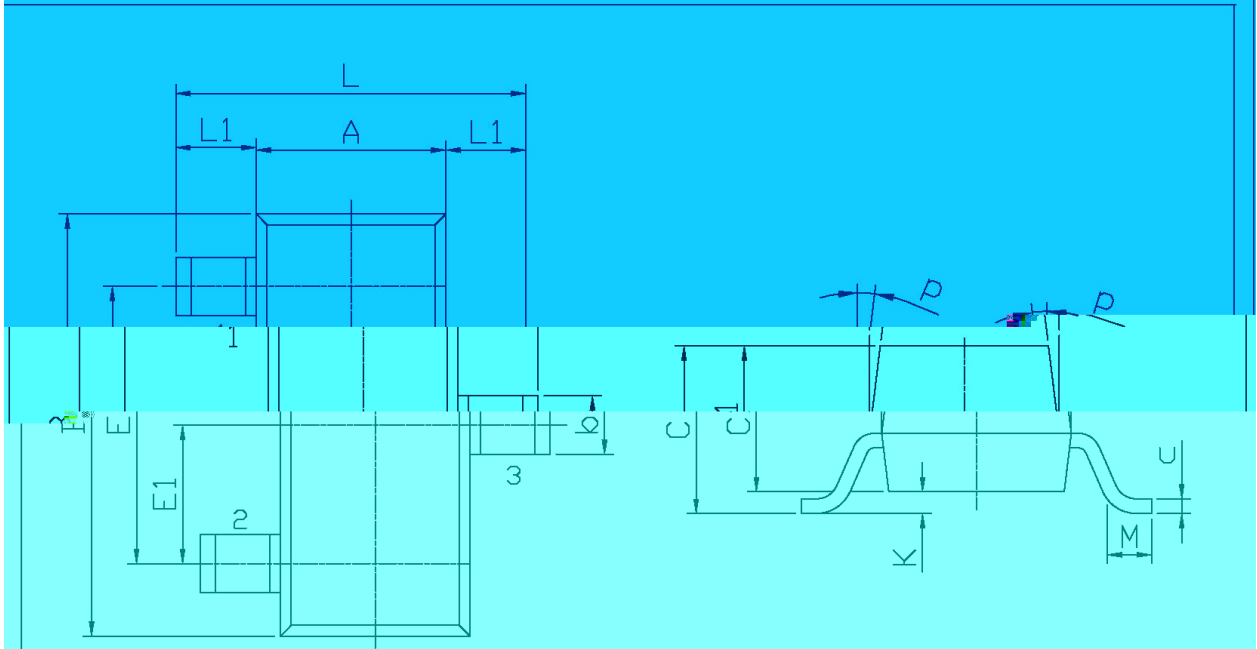
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	250	V
Collector to Emitter Voltage	V_{CEO}	250	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	50	mA
Peak Collector Current- Continuous	I_{CM}	100	mA
Base Current	I_B	50	mA
Collector Power Dissipation	P_C	250	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=200V$ $I_E=0$ $T_j=150$			10	μA
Collector Cut-Off Current	I_{CBO}	$V_{CB}=200V$ $I_E=0$			0.01	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			0.05	μA
DC Current Gain	h_{FE}	$V_{CE}=20V$ $I_C=25mA$	50			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=30mA$ $I_B=5.0mA$			0.6	V
Feedback Capacitance	C_{re}	$V_{CB}=30V$ $I_E=0$ $f=1.0MHz$			1.6	pF
Transition Frequency	f_T	$V_{CE}=10V$ $I_C=10mA$ $f=100MHz$	60			MHz

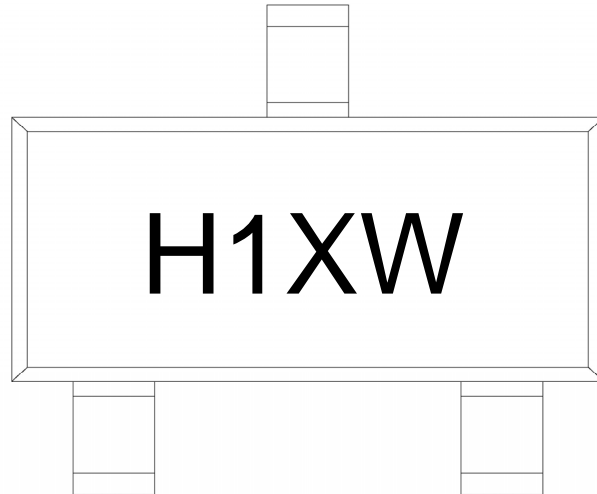


SOT-23

单位: mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
L	2.2	2.7	C	1.30Max	
L1	0.45	0.65	C1	0.90	1.20
A	1.15	1.50	c	0.05	0.20
R	2.70	2.70			



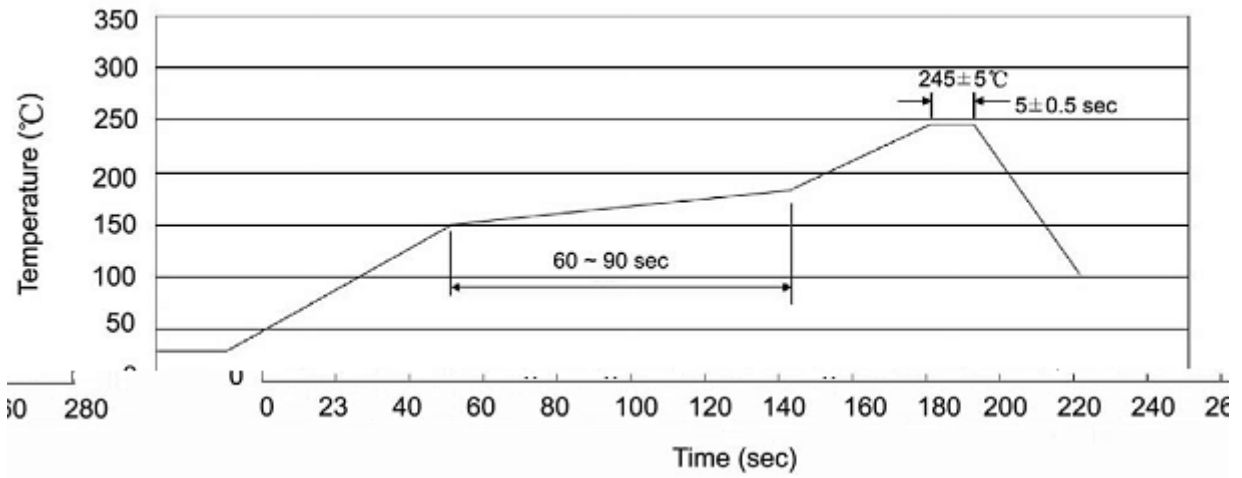
H

1XW

Note:

H: Company Code.

1XW: Product Type Code.

Temperature Profile for IR Reflow Soldering(Pb-Free)


Note:

- | | | | | | |
|---|-------|-----|----|-----------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245±5 | | | 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm ³)		